Microsemi Corporation - M1A3P600L-1FGG256 Datasheet

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	110592
Number of I/O	177
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	256-LBGA
Supplier Device Package	256-FPBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1a3p600l-1fgg256

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Using Sleep and Shutdown Modes in the System

Depending on the power supply and the components used in an application, there are many ways to power on or off the power supplies connected to the device. For example, Figure 2-6 shows how a microprocessor can be used to control a power FET. Microsemi recommends that power FETs with low resistance be used to perform the switching action.

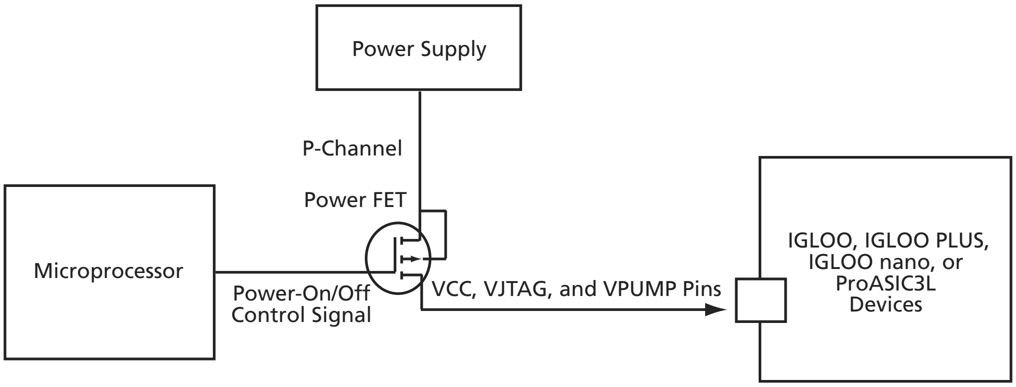

Figure 2-6 **• Controlling Power-On/-Off State Using Microprocessor and Power FET**

Figure 2-7 shows how a microprocessor can be used with a voltage regulator's shutdown pin to turn on or off the power supplies connected to the device.

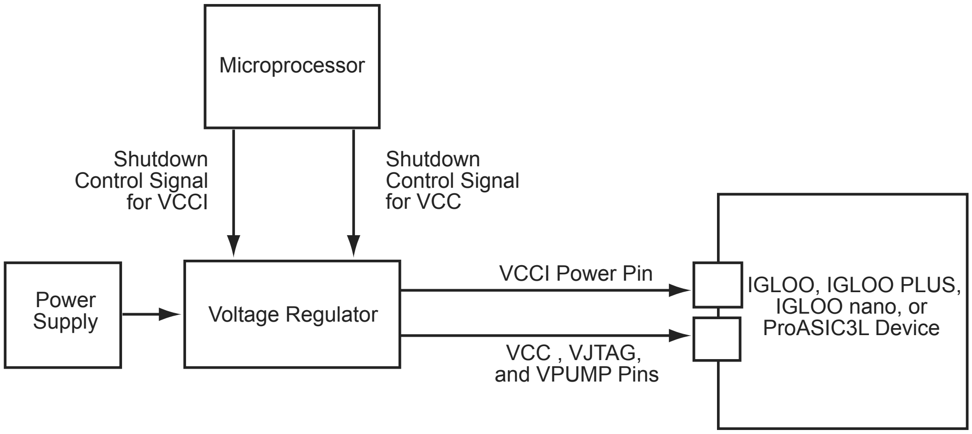

Figure 2-7 **• Controlling Power-On/-Off State Using Microprocessor and Voltage Regulator**

Power-Up/-Down Behavior

By design, all IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 I/Os are in tristate mode before device power-up. The I/Os remain tristated until the last voltage supply (V_{CC} or V_{CCI}) is powered to its activation level. After the last supply reaches its functional level, the outputs exit the tristate mode and drive the logic at the input of the output buffer. The behavior of user I/Os is independent of the V_{CC} and V_{CCI} sequence or the state of other voltage supplies of the FPGA (V_{PUMP} and V_{JTAG}). During power-down, device I/Os become tristated once the first power supply (V_{CC} or V_{CCI}) drops below its deactivation voltage level. The I/O behavior during power-down is also independent of voltage supply sequencing.

Figure 2-8 on page 34 shows a timing diagram when the V_{CC} power supply crosses the activation and deactivation trip points in a typical application when the V_{CC} power supply ramp-rate is 100 µs (ramping from 0 V to 1.5 V in this example). This is the timing diagram for the FPGA entering and exiting Sleep mode, as this function is dependent on powering V_{CC} down or up. Depending on the ramp-rate of the

- Avoid using pull-ups and pull-downs on I/Os because these resistors draw some current. Avoid driving resistive loads or bipolar transistors, since these draw a continuous current, thereby adding to the static current.
- When partitioning the design across multiple devices, minimize I/O usage among the devices.

Conclusion

Microsemi IGLOO, IGLOO nano, IGLOO PLUS, ProASIC3L, and RT ProASIC3 family architectures are designed to achieve ultra-low power consumption based on enhanced nonvolatile and live-at-power-up flash-based technology. Power consumption can be reduced further by using Flash*Freeze, Static (Idle), Sleep, and Shutdown power modes. All these features result in a low power, cost-effective, single-chip solution designed specifically for power-sensitive and battery-operated electronics applications.

Related Documents

Application Notes

Embedded SRAM Initialization Using External Serial EEPROM

http://www.microsemi.com/soc/documents/EmbeddedSRAMInit_AN.pdf

List of Changes

The following table lists critical changes that were made in each version of the chapter.

Date	Changes	Page
July 2010	This chapter is no longer published separately with its own part number and version but is now part of several FPGA fabric user's guides.	N/A
v2.3 (November 2009)	The "Sleep Mode" section was revised to state the VJTAG and VPUMP, as well as VCC, are grounded during Sleep mode (SAR 22517).	32
	Figure 2-6 • Controlling Power-On/-Off State Using Microprocessor and Power FET and Figure 2-7 • Controlling Power-On/-Off State Using Microprocessor and Voltage Regulator were revised to show that VJTAG and VPUMP are powered off during Sleep mode.	33
v2.2 (December 2008)	IGLOO nano devices were added as a supported family.	N/A
	The "Prototyping for IGLOO and ProASIC3L Devices Using ProASIC3" section was removed, as these devices are now in production.	N/A
	The "Additional Power Conservation Techniques" section was revised to add RT ProASIC3 devices.	41
v2.0 (October 2008)	The "Flash*Freeze Management FSM" section was updated with the following information: The FSM also asserts Flash_Freeze_Enabled whenever the device enters Flash*Freeze mode. This occurs after all housekeeping and clock gating functions have completed.	37

***Table 4-13* • 2-Bit Feedback MUX**

FBSEL<1:0> State	MUX Input Selected
0	Ground. Used for power-down mode in power-down logic block.
1	PLL VCO 0° phase shift
2	PLL delayed VCO 0° phase shift
3	N/A

***Table 4-14* • Programmable Delay Selection for Feedback Delay and Secondary Core Output Delays**

FBDLY<4:0>; DLYYB<4:0>; DLYYC<4:0> State	Delay Value
0	Typical delay = 600 ps
1	Typical delay = 760 ps
2	Typical delay = 920 ps
⋮	⋮
31	Typical delay = 5.56 ns

***Table 4-15* • Programmable Delay Selection for Global Clock Output Delays**

DLYGLA<4:0>; DLYGLB<4:0>; DLYGLC<4:0> State	Delay Value
0	Typical delay = 225 ps
1	Typical delay = 760 ps
2	Typical delay = 920 ps
⋮	⋮
31	Typical delay = 5.56 ns

***Table 4-16* • Fusion Dynamic CCC Clock Source Selection**

RXASEL	DYNASEL	Source of CLKA
1	0	RC Oscillator
1	1	Crystal Oscillator
RXBSEL	**DYNBSEL**	**Source of CLKB**
1	0	RC Oscillator
1	1	Crystal Oscillator
RXBSEL	**DYNCSEL**	**Source of CLKC**
1	0	RC Oscillator
1	1	Crystal Oscillator

***Table 4-17* • Fusion Dynamic CCC NGMUX Configuration**

GLMUXCFG<1:0>	NGMUX Select Signal	Supported Input Clocks to NGMUX
00	0	GLA
	1	GLC
01	0	GLA
	1	GLINT
10	0	GLC
	1	GLINT

```
  DYNCCC Core(.CLKA(CLKA), .EXTFB(GND), .POWERDOWN(POWERDOWN), .GLA(GLA), .LOCK(LOCK),
    .CLKB(CLKB), .GLB(GLB), .YB(), .CLKC(CLKC), .GLC(GLC), .YC(), .SDIN(SDIN),
    .SCLK(SCLK), .SSHIFT(SSHIFT), .SUPDATE(SUPDATE), .MODE(MODE), .SDOUT(SDOUT),
    .OADIV0(GND), .OADIV1(GND), .OADIV2(VCC), .OADIV3(GND), .OADIV4(GND), .OAMUX0(GND),
    .OAMUX1(GND), .OAMUX2(VCC), .DLYGLA0(GND), .DLYGLA1(GND), .DLYGLA2(GND),
    .DLYGLA3(GND), .DLYGLA4(GND), .OBDIV0(GND), .OBDIV1(GND), .OBDIV2(GND),
    .OBDIV3(GND), .OBDIV4(GND), .OBMUX0(GND), .OBMUX1(GND), .OBMUX2(GND), .DLYYB0(GND),
    .DLYYB1(GND), .DLYYB2(GND), .DLYYB3(GND), .DLYYB4(GND), .DLYGLB0(GND),
    .DLYGLB1(GND), .DLYGLB2(GND), .DLYGLB3(GND), .DLYGLB4(GND), .OCDIV0(GND),
    .OCDIV1(GND), .OCDIV2(GND), .OCDIV3(GND), .OCDIV4(GND), .OCMUX0(GND), .OCMUX1(GND),
    .OCMUX2(GND), .DLYYC0(GND), .DLYYC1(GND), .DLYYC2(GND), .DLYYC3(GND), .DLYYC4(GND),
    .DLYGLC0(GND), .DLYGLC1(GND), .DLYGLC2(GND), .DLYGLC3(GND), .DLYGLC4(GND),
    .FINDIV0(VCC), .FINDIV1(GND), .FINDIV2(VCC), .FINDIV3(GND), .FINDIV4(GND),
    .FINDIV5(GND), .FINDIV6(GND), .FBDIV0(GND), .FBDIV1(GND), .FBDIV2(GND),
    .FBDIV3(GND), .FBDIV4(GND), .FBDIV5(VCC), .FBDIV6(GND), .FBDLY0(GND), .FBDLY1(GND),
    .FBDLY2(GND), .FBDLY3(GND), .FBDLY4(GND), .FBSEL0(VCC), .FBSEL1(GND),
    .XDLYSEL(GND), .VCOSEL0(GND), .VCOSEL1(GND), .VCOSEL2(VCC));
  defparam Core.VCOFREQUENCY = 165.000;

endmodule
```

Delayed Clock Configuration

The CLKDLY macro can be generated with the desired delay and input clock source (Hardwired I/O, External I/O, or Core Logic), as in Figure 4-28.

Figure 4-28 **• Delayed Clock Configuration Dialog Box**

After setting all the required parameters, users can generate one or more PLL configurations with HDL or EDIF descriptions by clicking the **Generate** button. SmartGen gives the option of saving session results and messages in a log file:

```
****************
Macro Parameters
****************

Name                            : delay_macro
Family                          : ProASIC3
Output Format                   : Verilog
Type                            : Delayed Clock
Delay Index                     : 2
CLKA Source                     : Hardwired I/O

Total Clock Delay = 0.935 ns.

The resultant CLKDLY macro Verilog netlist is as follows:

module delay_macro(GL,CLK);

output GL;
input  CLK;
```

RD

This is the output data bus and is 18 bits wide. Not all 18 bits are valid in all configurations. Like the WD bus, high-order bits become unusable if the data width is less than 18. The output data on unused pins is undefined (Table 6-7).

***Table 6-7* • Input Data Signal Usage for Different Aspect Ratios**

D×W	WD/RD Unused
4k×1	WD[17:1], RD[17:1]
2k×2	WD[17:2], RD[17:2]
1k×4	WD[17:4], RD[17:4]
512×9	WD[17:9], RD[17:9]
256×18	–

ESTOP, FSTOP

ESTOP is used to stop the FIFO read counter from further counting once the FIFO is empty (i.e., the EMPTY flag goes HIGH). A HIGH on this signal inhibits the counting.

FSTOP is used to stop the FIFO write counter from further counting once the FIFO is full (i.e., the FULL flag goes HIGH). A HIGH on this signal inhibits the counting.

For more information on these signals, refer to the "ESTOP and FSTOP Usage" section.

FULL, EMPTY

When the FIFO is full and no more data can be written, the FULL flag asserts HIGH. The FULL flag is synchronous to WCLK to inhibit writing immediately upon detection of a full condition and to prevent overflows. Since the write address is compared to a resynchronized (and thus time-delayed) version of the read address, the FULL flag will remain asserted until two WCLK active edges after a read operation eliminates the full condition.

When the FIFO is empty and no more data can be read, the EMPTY flag asserts HIGH. The EMPTY flag is synchronous to RCLK to inhibit reading immediately upon detection of an empty condition and to prevent underflows. Since the read address is compared to a resynchronized (and thus time-delayed) version of the write address, the EMPTY flag will remain asserted until two RCLK active edges after a write operation removes the empty condition.

For more information on these signals, refer to the "FIFO Flag Usage Considerations" section on page 161.

AFULL, AEMPTY

These are programmable flags and will be asserted on the threshold specified by AFVAL and AEVAL, respectively.

When the number of words stored in the FIFO reaches the amount specified by AEVAL while reading, the AEMPTY output will go HIGH. Likewise, when the number of words stored in the FIFO reaches the amount specified by AFVAL while writing, the AFULL output will go HIGH.

AFVAL, AEVAL

The AEVAL and AFVAL pins are used to specify the almost-empty and almost-full threshold values. They are 12-bit signals. For more information on these signals, refer to the "FIFO Flag Usage Considerations" section on page 161.

FIFO Usage

ESTOP and FSTOP Usage

The ESTOP pin is used to stop the read counter from counting any further once the FIFO is empty (i.e., the EMPTY flag goes HIGH). Likewise, the FSTOP pin is used to stop the write counter from counting any further once the FIFO is full (i.e., the FULL flag goes HIGH).

The FIFO counters in the device start the count at zero, reach the maximum depth for the configuration (e.g., 511 for a 512×9 configuration), and then restart at zero. An example application for ESTOP, where the read counter keeps counting, would be writing to the FIFO once and reading the same content over and over without doing another write.

```
//
addr_counter counter_1 (.Clock(data_update), .Q(wr_addr), .Aset(rst_n),
  .Enable(enable));
addr_counter counter_2 (.Clock(test_clk), .Q(rd_addr), .Aset(rst_n),
  .Enable( test_active));

endmodule
```

Interface Block / UJTAG Wrapper

This example is a sample wrapper, which connects the interface block to the UJTAG and the memory blocks.

```
// WRAPPER
module top_init (TDI, TRSTB, TMS, TCK, TDO, test, test_clk, test_ out);

input TDI, TRSTB, TMS, TCK;
output TDO;
input test, test_clk;
output [3:0] test_out;

wire [7:0] IR;
wire reset, DR_shift, DR_cap, init_clk, DR_update, data_in, data_out;
wire clk_out, wen, ren;
wire [3:0] word_in, word_out;
wire [1:0] write_addr, read_addr;

UJTAG UJTAG_U1 (.UIREG0(IR[0]), .UIREG1(IR[1]), .UIREG2(IR[2]), .UIREG3(IR[3]),
  .UIREG4(IR[4]), .UIREG5(IR[5]), .UIREG6(IR[6]), .UIREG7(IR[7]), .URSTB(reset),
  .UDRSH(DR_shift), .UDRCAP(DR_cap), .UDRCK(init_clk), .UDRUPD(DR_update),
  .UT-DI(data_in), .TDI(TDI), .TMS(TMS), .TCK(TCK), .TRSTB(TRSTB), .TDO(TDO),
  .UT-DO(data_out));
mem_block RAM_block (.DO(word_out), .RCLOCK(clk_out), .WCLOCK(clk_out), .DI(word_in),
  .WRB(wen), .RDB(ren), .WAD-DR(write_addr), .RADDR(read_addr));
interface init_block (.IR(IR), .rst_n(reset), .data_shift(DR_shift), .clk_in(init_clk),
  .data_update(DR_update), .din_ser(data_in), .dout_ser(data_out), .test(test),
  .test_out(test_out), .test_clk(test_clk), .clk_out(clk_out), .wr_en(wen),
  .rd_en(ren), .write_word(word_in), .read_word(word_out), .rd_addr(read_addr),
  .wr_addr(write_addr));

endmodule
```

Address Counter

```
module addr_counter (Clock, Q, Aset, Enable);

input Clock;
output [1:0] Q;
input Aset;
input Enable;

reg [1:0] Qaux;

always @(posedge Clock or negedge Aset)
begin
  if (!Aset) Qaux <= 2'b11;
  else if (Enable) Qaux <= Qaux + 1;
end

assign Q = Qaux;

endmodule
```

Pipeline Register

```
module D_pipeline (Data, Clock, Q);

input [3:0] Data;
input Clock;
output [3:0] Q;

reg [3:0] Q;

always @ (posedge Clock) Q <= Data;

endmodule
```

4x4 RAM Block (created by SmartGen Core Generator)

```
module mem_block(DI,DO,WADDR,RADDR,WRB,RDB,WCLOCK,RCLOCK);

input [3:0] DI;
output [3:0] DO;
input [1:0] WADDR, RADDR;
input WRB, RDB, WCLOCK, RCLOCK;

wire WEBP, WEAP, VCC, GND;

VCC VCC_1_net(.Y(VCC));
GND GND_1_net(.Y(GND));
INV WEBUBBLEB(.A(WRB), .Y(WEBP));
RAM4K9 RAMBLOCK0(.ADDRA11(GND), .ADDRA10(GND), .ADDRA9(GND), .ADDRA8(GND),
  .ADDRA7(GND), .ADDRA6(GND), .ADDRA5(GND), .ADDRA4(GND), .ADDRA3(GND), .ADDRA2(GND),
  .ADDRA1(RADDR[1]), .ADDRA0(RADDR[0]), .ADDRB11(GND), .ADDRB10(GND), .ADDRB9(GND),
  .ADDRB8(GND), .ADDRB7(GND), .ADDRB6(GND), .ADDRB5(GND), .ADDRB4(GND), .ADDRB3(GND),
  .ADDRB2(GND), .ADDRB1(WADDR[1]), .ADDRB0(WADDR[0]), .DINA8(GND), .DINA7(GND),
  .DINA6(GND), .DINA5(GND), .DINA4(GND), .DINA3(GND), .DINA2(GND), .DINA1(GND),
  .DINA0(GND), .DINB8(GND), .DINB7(GND), .DINB6(GND), .DINB5(GND), .DINB4(GND),
  .DINB3(DI[3]), .DINB2(DI[2]), .DINB1(DI[1]), .DINB0(DI[0]), .WIDTHA0(GND),
  .WIDTHA1(VCC), .WIDTHB0(GND), .WIDTHB1(VCC), .PIPEA(GND), .PIPEB(GND),
  .WMODEA(GND), .WMODEB(GND), .BLKA(WEAP), .BLKB(WEBP), .WENA(VCC), .WENB(GND),
  .CLKA(RCLOCK), .CLKB(WCLOCK), .RESET(VCC), .DOUTA8(), .DOUTA7(), .DOUTA6(),
  .DOUTA5(), .DOUTA4(), .DOUTA3(DO[3]), .DOUTA2(DO[2]), .DOUTA1(DO[1]),
  .DOUTA0(DO[0]), .DOUTB8(), .DOUTB7(), .DOUTB6(), .DOUTB5(), .DOUTB4(), .DOUTB3(),
  .DOUTB2(), .DOUTB1(), .DOUTB0());
INV WEBUBBLEA(.A(RDB), .Y(WEAP));

endmodule
```

Date	Changes	Page
v1.1 (continued)	Table 6-1 • Flash-Based FPGAs and associated text were updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	150
	The text introducing Table 6-8 • Memory Availability per IGLOO and ProASIC3 Device was updated to replace "A3P030 and AGL030" with "15 k and 30 k gate devices." Table 6-8 • Memory Availability per IGLOO and ProASIC3 Device was updated to remove AGL400 and AGLE1500 and include IGLOO PLUS and ProASIC3L devices.	162

- In Active and Static modes:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High
  - Output buffers with pull-up, driven Low
  - Output buffers with pull-down, driven High
  - Tristate buffers with pull-up, driven Low
  - Tristate buffers with pull-down, driven High
- In Flash*Freeze mode:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High

Electrostatic Discharge Protection

Low power flash devices are tested per JEDEC Standard JESD22-A114-B.

These devices contain clamp diodes at every I/O, global, and power pad. Clamp diodes protect all device pads against damage from ESD as well as from excessive voltage transients.

All IGLOO and ProASIC3 devices are tested to the Human Body Model (HBM) and the Charged Device Model (CDM).

Each I/O has two clamp diodes. One diode has its positive (P) side connected to the pad and its negative (N) side connected to VCCI. The second diode has its P side connected to GND and its N side connected to the pad. During operation, these diodes are normally biased in the off state, except when transient voltage is significantly above VCCI or below GND levels.

In 30K gate devices, the first diode is always off. In other devices, the clamp diode is always on and cannot be switched off.

By selecting the appropriate I/O configuration, the diode is turned on or off. Refer to Table 7-12 on page 193 for more information about the I/O standards and the clamp diode.

The second diode is always connected to the pad, regardless of the I/O configuration selected.

Table 7-12 **• I/O Hot-Swap and 5 V Input Tolerance Capabilities in IGLOO and ProASIC3 Devices**

I/O Assignment	**Clamp Diode** [1]		**Hot Insertion**		**5 V Input Tolerance** [2]		**Input and Output Buffer**
	AGL030 and A3P030	**Other IGLOO and ProASIC3 Devices**	**AGL015 and AGL030**	**Other IGLOO Devices and All ProASIC3**	**AGL030 and A3P030**	**Other IGLOO and ProASIC3 Devices**	
3.3 V LVTTL/LVCMOS	No	Yes	Yes	No	Yes [2]	Yes [2]	Enabled/Disabled
3.3 V PCI, 3.3 V PCI-X	N/A	Yes	N/A	No	N/A	Yes [2]	Enabled/Disabled
LVCMOS 2.5 V [5]	No	Yes	Yes	No	Yes [2]	Yes [4]	Enabled/Disabled
LVCMOS 2.5 V / 5.0 V [6]	N/A	Yes	N/A	No	N/A	Yes [4]	Enabled/Disabled
LVCMOS 1.8 V	No	Yes	Yes	No	No	No	Enabled/Disabled
LVCMOS 1.5 V	No	Yes	Yes	No	No	No	Enabled/Disabled
Differential, LVDS/ B-LVDS/M-LVDS/LVPECL	N/A	Yes	N/A	No	N/A	No	Enabled/Disabled

Notes:

1. *The clamp diode is always off for the AGL030 and A3P030 device and always active for other IGLOO and ProASIC3 devices.*
2. *Can be implemented with an external IDT bus switch, resistor divider, or Zener with resistor.*
3. *Refer to Table 7-8 on page 189 to Table 7-11 on page 190 for device-compliant information.*
4. *Can be implemented with an external resistor and an internal clamp diode.*
5. *The LVCMOS 2.5 V I/O standard is supported by the 30 k gate devices only; select the LVCMOS25 macro.*
6. *The LVCMOS 2.5 V / 5.0 V I/O standard is supported by all IGLOO and ProASIC3 devices except 30K gate devices; select the LVCMOS5 macro.*

Board-Level Considerations

Low power flash devices have robust I/O features that can help in reducing board-level components. The devices offer single-chip solutions, which makes the board layout simpler and more immune to signal integrity issues. Although, in many cases, these devices resolve board-level issues, special attention should always be given to overall signal integrity. This section covers important board-level considerations to facilitate optimum device performance.

Termination

Proper termination of all signals is essential for good signal quality. Nonterminated signals, especially clock signals, can cause malfunctioning of the device.

For general termination guidelines, refer to the *Board-Level Considerations* application note for Microsemi FPGAs. Also refer to the "Pin Descriptions" chapter of the appropriate datasheet for termination requirements for specific pins.

Low power flash I/Os are equipped with on-chip pull-up/-down resistors. The user can enable these resistors by instantiating them either in the top level of the design (refer to the *IGLOO, Fusion, and ProASIC3 Macro Library Guide* for the available I/O macros with pull-up/-down) or in the I/O Attribute Editor in Designer if generic input or output buffers are instantiated in the top level. Unused I/O pins are configured as inputs with pull-up resistors.

As mentioned earlier, low power flash devices have multiple programmable drive strengths, and the user can eliminate unwanted overshoot and undershoot by adjusting the drive strengths.

Power-Up Behavior

Low power flash devices are power-up/-down friendly; i.e., no particular sequencing is required for power-up and power-down. This eliminates extra board components for power-up sequencing, such as a power-up sequencer.

During power-up, all I/Os are tristated, irrespective of I/O macro type (input buffers, output buffers, I/O buffers with weak pull-ups or weak pull-downs, etc.). Once I/Os become activated, they are set to the user-selected I/O macros. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details.

Drive Strength

Low power flash devices have up to seven programmable output drive strengths. The user can select the drive strength of a particular output in the I/O Attribute Editor or can instantiate a specialized I/O macro, such as OUTBUF_S_12 (slew = low, out_drive = 12 mA).

The maximum available drive strength is 24 mA per I/O. Though no I/O should be forced to source or sink more than 24 mA indefinitely, I/Os may handle a higher amount of current (refer to the device IBIS model for maximum source/sink current) during signal transition (AC current). Every device package has its own power dissipation limit; hence, power calculation must be performed accurately to determine how much current can be tolerated per I/O within that limit.

I/O Interfacing

Low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected (refer to the "5 V Input and Output Tolerance" section on page 194). Along with other low-voltage I/O macros, this 5 V tolerance makes these devices suitable for many types of board component interfacing.

Table 7-19 shows some high-level interfacing examples using low power flash devices.

***Table 7-19* • High-Level Interface Examples**

Interface	Clock		I/O			
	Type	**Frequency**	**Type**	**Signals In**	**Signals Out**	**Data I/O**
GM	Src Sync	125 MHz	LVTTL	8	8	125 Mbps
TBI	Src Sync	125 MHz	LVTTL	10	10	125 Mbps
XSBI	Src Sync	644 MHz	LVDS	16	16	644 Mbps
XGMI	Src Sync DDR	156 MHz	HSTL1	32	32	312 Mbps
FlexBus 3	Sys Sync	104 MHz	LVTTL	≤ 32	≤ 32	≤ 104
Pos-PHY3/SPI-3	Sys Sync	104	LVTTL	8, 16, 32	8, 16, 32	≤ 104 Mbps
FlexBus 4/SPI-4.1	Src Sync	200 MHz	HSTL1	16,64	16,64	200 Mbps
Pos-PHY4/SPI-4.2	Src Sync DDR	≥ 311 MHz	LVDS	16	16	≥ 622 Mbps
SFI-4.1	Src Sync	622 MHz	LVDS	16	16	622 Mbps
CSIX L1	Sys Sync	≤ 250 MHz	HSTL1	32,64,96,128	32,64,96,128	≤ 250 Mbps
Hyper Transport	Sys Sync DDR	≤ 800 MHz	LVDS	2,4,8,16	2,4,8,16	≤ 1.6 Gbps
Rapid I/O Parallel	Sys Sync DDR	250 MHz – 1 GHz	LVDS	8,16	8,16	≤ 2 Gbps
Star Fabric	CDR		LVDS	4	4	622 Mbps

Note: Sys Sync = System Synchronous Clocking, Src Sync = Source Synchronous Clocking, and CDR = Clock and Data Recovery.

Conclusion

IGLOO and ProASIC3 support for multiple I/O standards minimizes board-level components and makes possible a wide variety of applications. The Microsemi Designer software, integrated with Libero SoC, presents a clear visual display of I/O assignments, allowing users to verify I/O and board-level design requirements before programming the device. The IGLOO and ProASIC3 device I/O features and functionalities ensure board designers can produce low-cost and low power FPGA applications fulfilling the complexities of contemporary design needs.

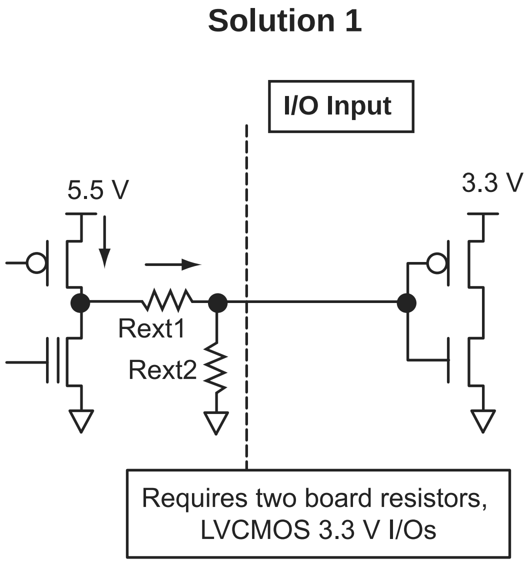

Figure 8-10 • **Solution 1**

Solution 2

The board-level design must ensure that the reflected waveform at the pad does not exceed the voltage overshoot/undershoot limits provided in the datasheet. This is a requirement to ensure long-term reliability.

This scheme will also work for a 3.3 V PCI/PCI-X configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the external resistors and Zener, as shown in Figure 8-11. Relying on the diode clamping would create an excessive pad DC voltage of 3.3 V + 0.7 V = 4 V.

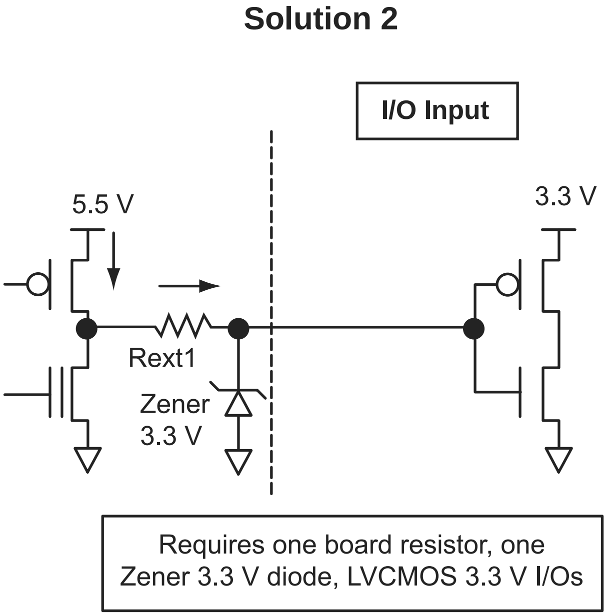

Figure 8-11 • **Solution 2**

Power-Up Behavior

Low power flash devices are power-up/-down friendly; i.e., no particular sequencing is required for power-up and power-down. This eliminates extra board components for power-up sequencing, such as a power-up sequencer.

During power-up, all I/Os are tristated, irrespective of I/O macro type (input buffers, output buffers, I/O buffers with weak pull-ups or weak pull-downs, etc.). Once I/Os become activated, they are set to the user-selected I/O macros. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 373 for details.

Drive Strength

Low power flash devices have up to seven programmable output drive strengths. The user can select the drive strength of a particular output in the I/O Attribute Editor or can instantiate a specialized I/O macro, such as OUTBUF_S_12 (slew = low, out_drive = 12 mA).

The maximum available drive strength is 24 mA per I/O. Though no I/O should be forced to source or sink more than 24 mA indefinitely, I/Os may handle a higher amount of current (refer to the device IBIS model for maximum source/sink current) during signal transition (AC current). Every device package has its own power dissipation limit; hence, power calculation must be performed accurately to determine how much current can be tolerated per I/O within that limit.

I/O Interfacing

Low power flash devices are 5 V–input– and 5 V–output–tolerant if certain I/O standards are selected (refer to the "5 V Input and Output Tolerance" section on page 232). Along with other low-voltage I/O macros, this 5 V tolerance makes these devices suitable for many types of board component interfacing.

Table 8-19 shows some high-level interfacing examples using low power flash devices.

Table 8-19 **• High-Level Interface Examples**

	Clock		I/O			
Interface	**Type**	**Frequency**	**Type**	**Signals In**	**Signals Out**	**Data I/O**
GM	Src Sync	125 MHz	LVTTL	8	8	125 Mbps
TBI	Src Sync	125 MHz	LVTTL	10	10	125 Mbps
XSBI	Src Sync	644 MHz	LVDS	16	16	644 Mbps
XGMI	Src Sync DDR	156 MHz	HSTL1	32	32	312 Mbps
FlexBus 3	Sys Sync	104 MHz	LVTTL	≤ 32	≤ 32	≤ 104
Pos-PHY3/SPI-3	Sys Sync	104	LVTTL	8,16,32	8,16,32	≤ 104 Mbps
FlexBus 4/SPI-4.1	Src Sync	200 MHz	HSTL1	16,64	16,64	200 Mbps
Pos-PHY4/SPI-4.2	Src Sync DDR	≥ 311 MHz	LVDS	16	16	≥ 622 Mbps
SFI-4.1	Src Sync	622 MHz	LVDS	16	16	622 Mbps
CSIX L1	Sys Sync	≤ 250 MHz	HSTL1	32,64,96,128	32,64,96,128	≤ 250 Mbps
Hyper Transport	Sys Sync DDR	≤ 800 MHz	LVDS	2,4,8,16	2,4,8,16	≤ 1.6 Gbps
Rapid I/O Parallel	Sys Sync DDR	250 MHz – 1 GHz	LVDS	8,16	8,16	≤ 2 Gbps
Star Fabric	CDR		LVDS	4	4	622 Mbps

Note: Sys Sync = System Synchronous Clocking, Src Sync = Source Synchronous Clocking, and CDR = Clock and Data Recovery.

List of Changes

The following table lists critical changes that were made in each revision of the document.

Date	Changes	Page
August 2012	The notes in Table 9-2 • Designer State (resulting from I/O attribute modification) were revised to clarify which device families support programmable input delay (SAR 39666).	253
June 2011	Figure 9-2 • SmartGen Catalog was updated (SAR 24310). Figure 8-3 • Expanded I/O Section and the step associated with it were deleted to reflect changes in the software.	254
	The following rule was added to the "VREF Rules for the Implementation of Voltage-Referenced I/O Standards" section: Only minibanks that contain input or bidirectional I/Os require a VREF. A VREF is not needed for minibanks composed of output or tristated I/Os (SAR 24310).	265
July 2010	Notes were added where appropriate to point out that IGLOO nano and ProASIC3 nano devices do not support differential inputs (SAR 21449).	N/A
v1.4 (December 2008)	IGLOO nano and ProASIC3 nano devices were added to Table 9-1 • Flash-Based FPGAs.	252
	The notes for Table 9-2 • Designer State (resulting from I/O attribute modification) were revised to indicate that skew control and input delay do not apply to nano devices.	253
v1.3 (October 2008)	The "Flash FPGAs I/O Support" section was revised to include new families and make the information more concise.	252
v1.2 (June 2008)	The following changes were made to the family descriptions in Table 9-1 • Flash-Based FPGAs: • ProASIC3L was updated to include 1.5 V. • The number of PLLs for ProASIC3E was changed from five to six.	252
v1.1 (March 2008)	This document was previously part of the *I/O Structures in IGLOO and ProASIC3 Devices* document. The content was separated and made into a new document.	N/A
	Table 9-2 • Designer State (resulting from I/O attribute modification) was updated to include note 2 for IGLOO PLUS.	253

3. A single STAPL file or multiple STAPL files with multiple FlashROM contents. A single STAPL file will be generated if the device serialization feature is not used. You can program the whole FlashROM or selectively program individual pages.
4. A single STAPL file to configure the security settings for the device, such as the AES Key and/or Pass Key.

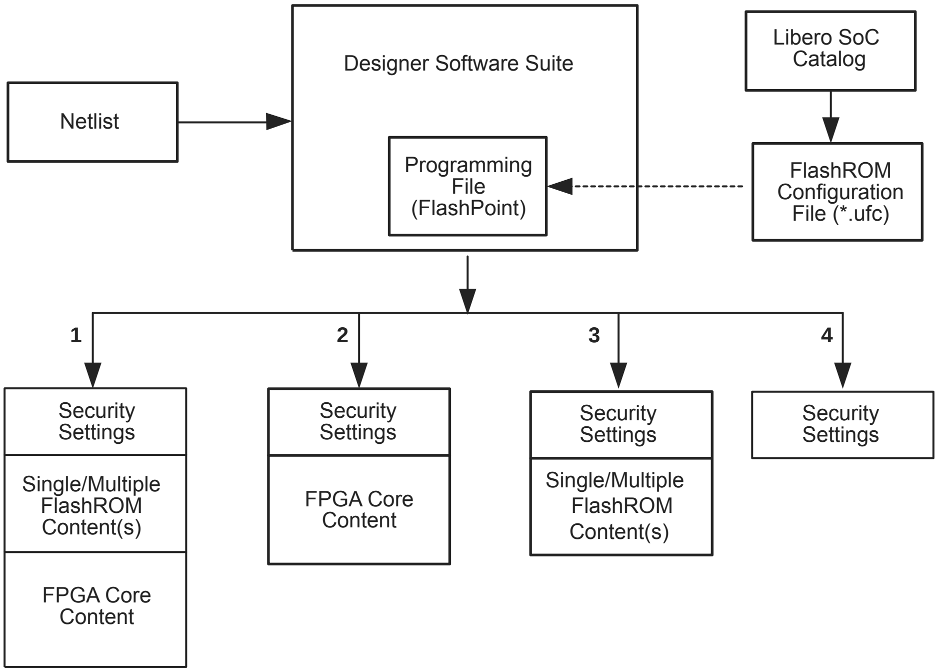

Figure 13-4 **• Flexible Programming File Generation for Different Applications**

Programming Solution

For device programming, any IEEE 1532–compliant programmer can be used; however, the FlashPro4/3/3X programmer must be used to control the low power flash device's rich security features and FlashROM programming options. The FlashPro4/3/3X programmer is a low-cost portable programmer for the Microsemi flash families. It can also be used with a powered USB hub for parallel programming. General specifications for the FlashPro4/3/3X programmer are as follows:

- Programming clock – TCK is used with a maximum frequency of 20 MHz, and the default frequency is 4 MHz.
- Programming file – STAPL
- Daisy chain – Supported. You can use the ChainBuilder software to build the programming file for the chain.
- Parallel programming – Supported. Multiple FlashPro4/3/3X programmers can be connected together using a powered USB hub or through the multiple USB ports on the PC.
- Power supply – The target board must provide VCC, VCCI, VPUMP, and VJTAG during programming. However, if there is only one device on the target board, the FlashPro4/3/3X programmer can generate the required VPUMP voltage from the USB port.

useless to the thief. To learn more about the low power flash devices' security features, refer to the "Security in Low Power Flash Devices" section on page 301.

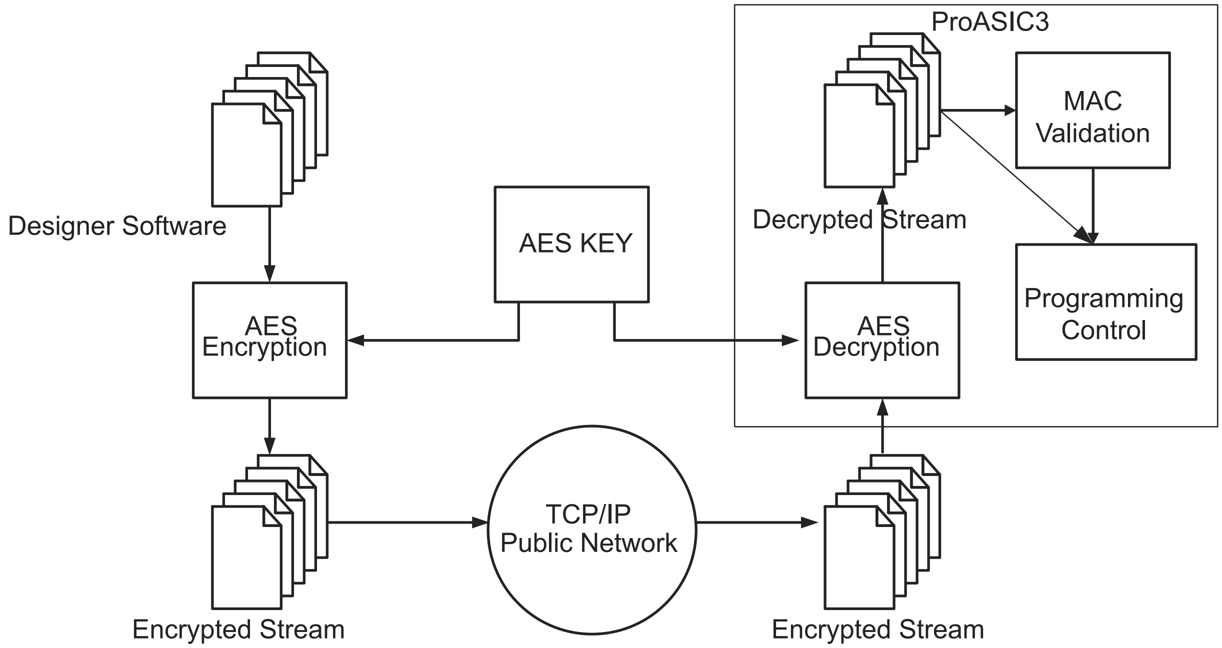

Figure 15-5 • **ProASIC3 Device Encryption Flow**

Conclusion

The Fusion, IGLOO, and ProASIC3 FPGAs are ideal for applications that require field upgrades. The single-chip devices save board space by eliminating the need for EEPROM. The built-in AES with MAC enables transmission of programming data over any network without fear of design theft. Fusion, IGLOO, and ProASIC3 FPGAs are IEEE 1532–compliant and support STAPL, making the target programming software easy to implement.

17 – UJTAG Applications in Microsemi's Low Power Flash Devices

Introduction

In Fusion, IGLOO, and ProASIC3 devices, there is bidirectional access from the JTAG port to the core VersaTiles during normal operation of the device (Figure 17-1). User JTAG (UJTAG) is the ability for the design to use the JTAG ports for access to the device for updates, etc. While regular JTAG is used, the UJTAG tiles, located at the southeast area of the die, are directly connected to the JTAG Test Access Port (TAP) Controller in normal operating mode. As a result, all the functional blocks of the device, such as Clock Conditioning Circuits (CCCs) with PLLs, SRAM blocks, embedded FlashROM, flash memory blocks, and I/O tiles, can be reached via the JTAG ports. The UJTAG functionality is available by instantiating the UJTAG macro directly in the source code of a design. Access to the FPGA core VersaTiles from the JTAG ports enables users to implement different applications using the TAP Controller (JTAG port). This document introduces the UJTAG tile functionality and discusses a few application examples. However, the possible applications are not limited to what is presented in this document. UJTAG can serve different purposes in many designs as an elementary or auxiliary part of the design. For detailed usage information, refer to the "Boundary Scan in Low Power Flash Devices" section on page 357.

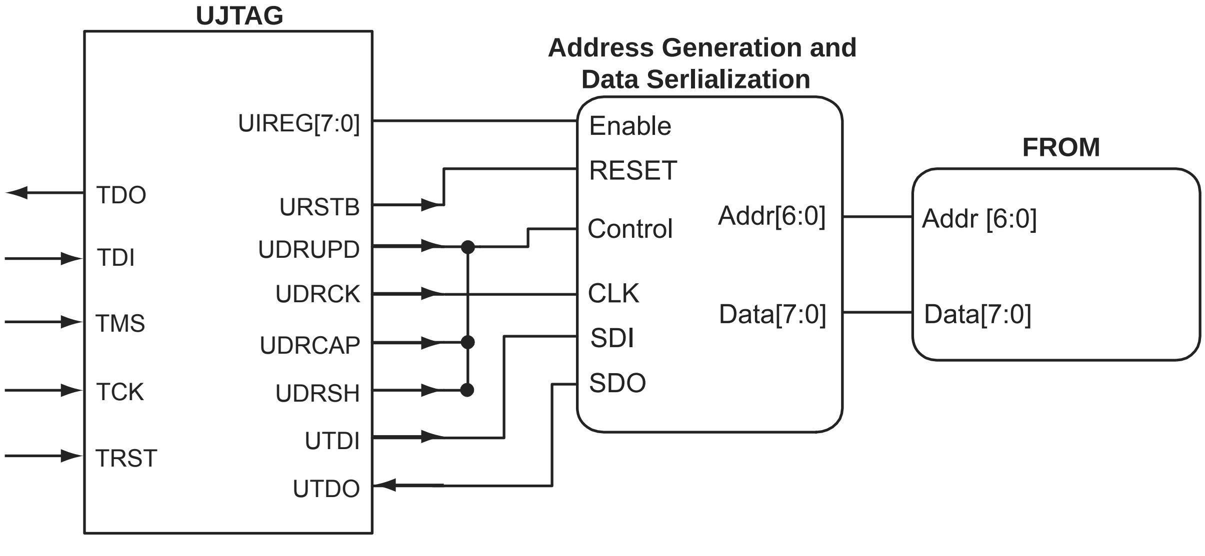

Figure 17-1 • **Block Diagram of Using UJTAG to Read FlashROM Contents**

18 – Power-Up/-Down Behavior of Low Power Flash Devices

Introduction

Microsemi’s low power flash devices are flash-based FPGAs manufactured on a 0.13 µm process node. These devices offer a single-chip, reprogrammable solution and support Level 0 live at power-up (LAPU) due to their nonvolatile architecture.

Microsemi's low power flash FPGA families are optimized for logic area, I/O features, and performance. IGLOO® devices are optimized for power, making them the industry's lowest power programmable solution. IGLOO PLUS FPGAs offer enhanced I/O features beyond those of the IGLOO ultra-low power solution for I/O-intensive low power applications. IGLOO nano devices are the industry's lowest-power cost-effective solution. ProASIC3®L FPGAs balance low power with high performance. The ProASIC3 family is Microsemi's high-performance flash FPGA solution. ProASIC3 nano devices offer the lowest-cost solution with enhanced I/O capabilities.

Microsemi’s low power flash devices exhibit very low transient current on each power supply during power-up. The peak value of the transient current depends on the device size, temperature, voltage levels, and power-up sequence.

The following devices can have inputs driven in while the device is not powered:

- IGLOO (AGL015 and AGL030)
- IGLOO nano (all devices)
- IGLOO PLUS (AGLP030, AGLP060, AGLP125)
- IGLOOe (AGLE600, AGLE3000)
- ProASIC3L (A3PE3000L)
- ProASIC3 (A3P015, A3P030)
- ProASIC3 nano (all devices)
- ProASIC3E (A3PE600, A3PE1500, A3PE3000)
- Military ProASIC3EL (A3PE600L, A3PE3000L, but not A3P1000)
- RT ProASIC3 (RT3PE600L, RT3PE3000L)

The driven I/Os do not pull up power planes, and the current draw is limited to very small leakage current, making them suitable for applications that require cold-sparing. These devices are hot-swappable, meaning they can be inserted in a live power system.[1]

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[1] *For more details on the levels of hot-swap compatibility in Microsemi’s low power flash devices, refer to the "Hot-Swap Support" section in the I/O Structures chapter of the FPGA fabric user’s guide for the device you are using.*

I/O Behavior at Power-Up/-Down

This section discusses the behavior of device I/Os, used and unused, during power-up/-down of V_{CC} and V_{CCI}. As mentioned earlier, VMVx and V_{CCI}Bx are tied together, and therefore, inputs and outputs are powered up/down at the same time.

I/O State during Power-Up/-Down

This section discusses the characteristics of I/O behavior during device power-up and power-down. Before the start of power-up, all I/Os are in tristate mode. The I/Os will remain tristated during power-up until the last voltage supply (VCC or VCCI) is powered to its functional level (power supply functional levels are discussed in the "Power-Up to Functional Time" section on page 378). After the last supply reaches the functional level, the outputs will exit the tristate mode and drive the logic at the input of the output buffer. Similarly, the input buffers will pass the external logic into the FPGA fabric once the last supply reaches the functional level. The behavior of user I/Os is independent of the VCC and VCCI sequence or the state of other voltage supplies of the FPGA (VPUMP and VJTAG). Figure 18-2 shows the output buffer driving HIGH and its behavior during power-up with 10 kΩ external pull-down. In Figure 18-2, VCC is powered first, and VCCI is powered 5 ms after VCC. Figure 18-3 on page 378 shows the state of the I/O when VCCI is powered about 5 ms before VCC. In the circuitry shown in Figure 18-3 on page 378, the output is externally pulled down.

During power-down, device I/Os become tristated once the first power supply (VCC or VCCI) drops below its brownout voltage level. The I/O behavior during power-down is also independent of voltage supply sequencing.

Figure 18-2 • **I/O State when VCC Is Powered before VCCI**